TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE (PCT PROCESS)

# 2 S C 2 7 1 4

HIGH FREQUENCY AMPLIFIER APPLICATIONS FM, RF, MIX, IF AMPLIFIER APPLICATIONS

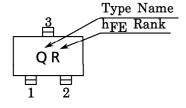
• Small Reverse Transfer Capacitance : C<sub>re</sub>=0.7pF (Typ.)

• Low Noise Figure: NF=2.5dB (Typ.) (f=100MHz)

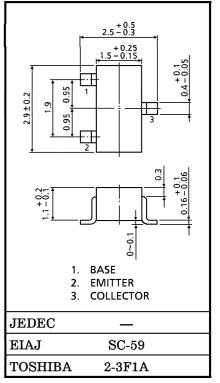
## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	40	V
Collector-Emitter Voltage	$v_{CEO}$	30	V
Emitter-Base Voltage	$V_{ m EBO}$	4	V
Collector Current	$I_{\mathbf{C}}$	20	mA
Base Current	$I_{\mathbf{B}}$	4	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	100	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

## Marking



#### Unit in mm



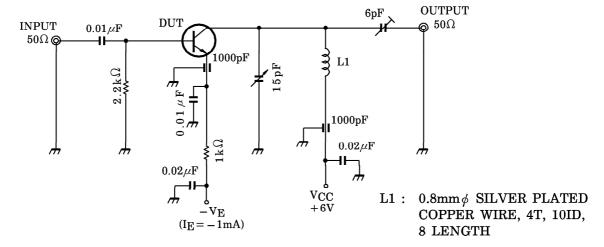
Weight: 0.012g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 18V, I_{E} = 0$	_	_	0.5	$\mu$ A
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB}=4V, I_{C}=0$		_	0.5	$\mu$ A
DC Current Gain	h <sub>FE</sub> (Note)	$V_{ m CE}$ =6V, I $_{ m C}$ =1mA	40	_	200	
Reverse Transfer Capacitance	$\mathrm{c}_{\mathrm{re}}$	$V_{CB}=6V, f=1MHz$	_	0.7	_	pF
Transition Frequency	$\mathbf{f_T}$	$V_{CE}=6V, I_{C}=1mA$	_	550	_	MHz
Collector-Base Time Constant	$C_c$ . rbb'		_	_	30	ps
Noise Figure	NF	$V_{CE}=6V, I_{E}=-1mA$	_	2.5	5.0	dB
Power Gain	$G_{ m pe}$	f=100MHz, Fig.	17	23	_	dB

(Note) hFE Classification  $R:40{\sim}80$ ,  $O:70{\sim}140$ ,  $Y:100{\sim}200$ 

Fig. NF, Gpe TEST CIRCUIT



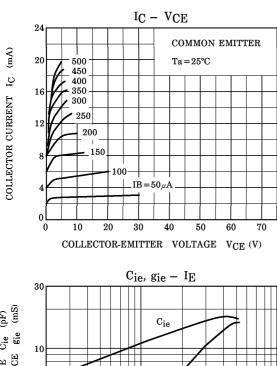
## y PARAMETER (Typ.)

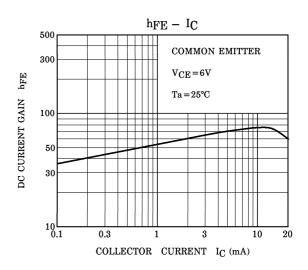
# (1) COMMON EMITTER ( $V_{CE} = 6V$ , $I_E = -1mA$ , f = 100MHz)

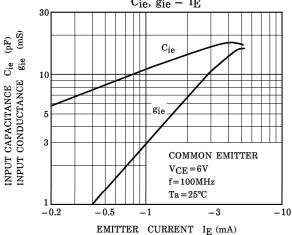
CHARACTERISTIC	SYMBOL	TYP.	UNIT
Input Conductance	gie	2.9	mS
Input Capacitance	Cie	10.2	pF
Reverse Transfer Admittance	y <sub>re</sub>	0.33	mS
Phase Angle of Reverse Transfer Adimttance	$\theta_{ extbf{re}}$	-90	٥
Forward Transfer Admittance	$ y_{\mathrm{fe}} $	40	mS
Phase Angle of Forward Transfer Admittance	$\theta_{\mathbf{fe}}$	-20	0
Output Conductance	goe	45	$\mu$ S
Output Capacitance	Coe	1.1	pF

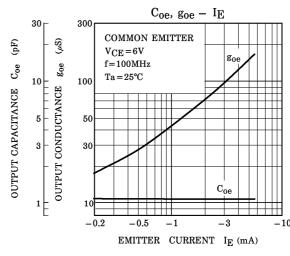
# (2) COMMON BASE ( $V_{CE} = 6V$ , $I_E = -1mA$ , f = 100MHz)

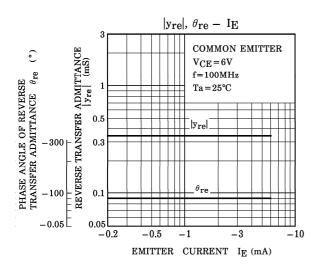
CHARACTERISTIC	SYMBOL	TYP.	UNIT
Input Conductance	gib	34	mS
Input Capacitance	$C_{\mathbf{ib}}$	-10	pF
Reverse Transfer Admittance	$ y_{rb} $	0.27	mS
Phase Angle of Reverse Transfer Adimttance	$ heta_{ extbf{rb}}$	-105	0
Forward Transfer Admittance	yfb	34	mS
Phase Angle of Forward Transfer Admittance	$ heta_{\mathbf{fb}}$	165	٥
Output Conductance	gob	45	$\mu$ S
Output Capacitance	$C_{ob}$	1.1	pF

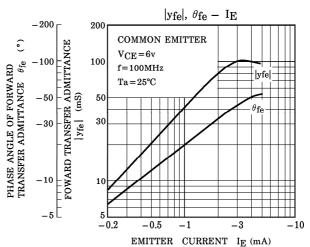


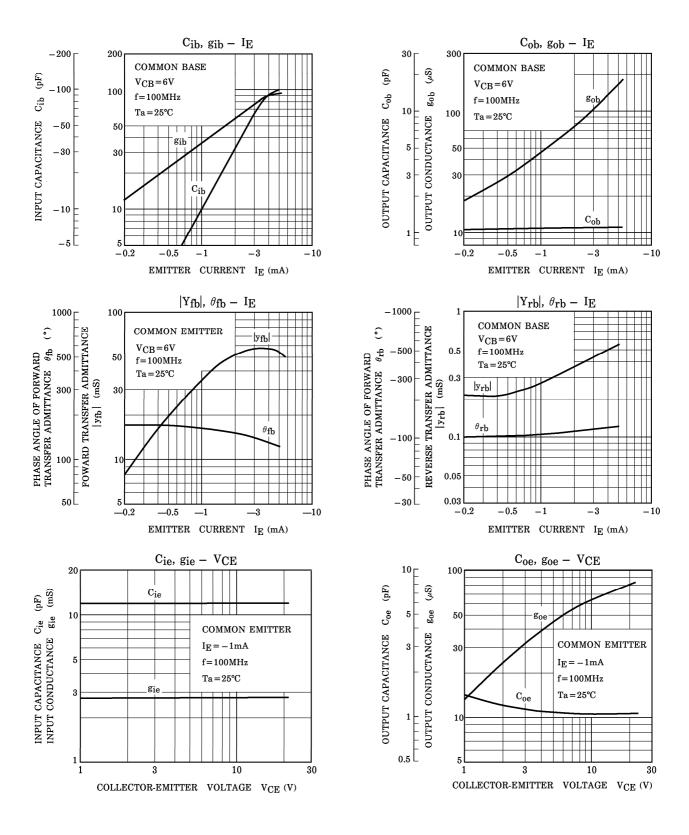


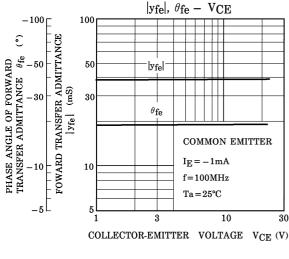


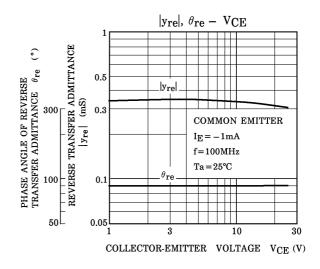


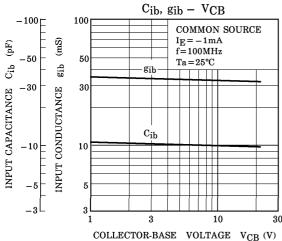


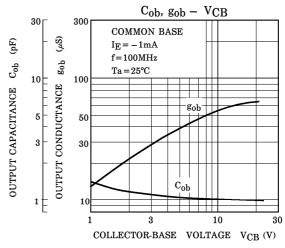


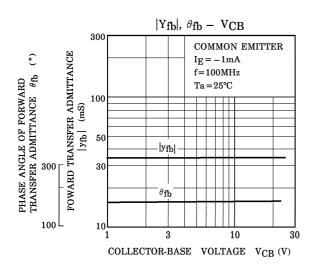


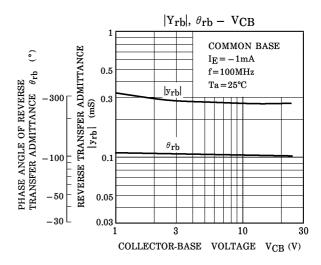


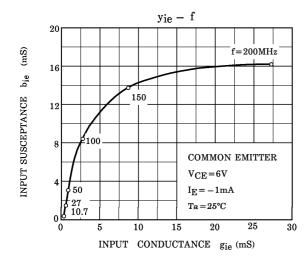


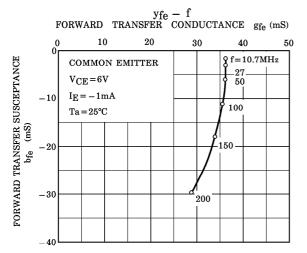


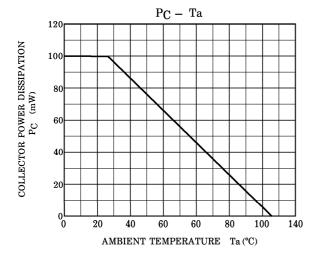


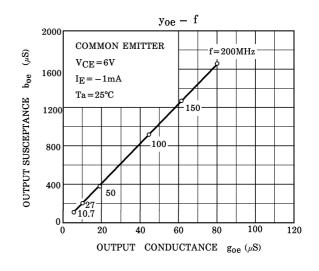


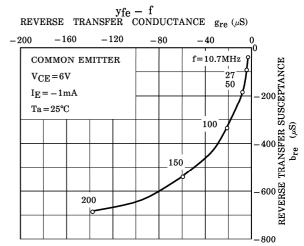












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